



ABSTRACT OF THE DISCLOSURE

The present invention relates to a technique for improving a withstanding voltage of operation of a semiconductor device. The present invention provides a semiconductor device including a gate electrode formed on a semiconductor substrate via the first and the second gate oxide films and source-drain regions of low and high concentration formed adjacent to the gate electrode. A diffusion region width of the source-drain regions of low concentration on the source region side is smaller than at least that on the drain region side. A source region of high concentration is formed adjacent to one end of the gate electrode. A drain region of high concentration is formed at a position distant from the other end of the gate electrode by a predetermined interval.

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